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compound semiconductors such as zinc selenide (ZnSe), zinc sulfide (ZnS) and zinc oxide(ZnO) may also be used.--

IN THE CLAIMS:

Please amend claims 1, 3-5, 7, 8, 12, 13, 15 and 16. The amendments are based on Fig. 1 and the description of Fig. 1 in the present specification.

1. (Currently amended) A semiconductor laser device [characterized by] comprising:
a resonant cavity [made up of a plurality of semiconductor layers] disposed between a n-type compound semiconductor layer and a p-type compound semiconductor layer at the main surface and the opposite surface, a light is emitted along the interfaces of the n-type compound semiconductor layer and the p-type compound semiconductor layer by applying a voltage to each compound semiconductor layer; and
a reflective film[, which contains niobium oxide and is formed on] adhered to an end facet of the resonant cavity,

wherein the reflective film is composed of a first dielectric layer and a second dielectric layer containing niobium oxide.

3. (Currently amended) The semiconductor laser device of Claim 1, [characterized in that] wherein the [semiconductor layers] n-type compound semiconductor layer and the p-type semiconductor layer are made of Group III - V nitride semiconductors.

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4. (Currently amended) [A semiconductor laser device characterized by comprising:

a resonant cavity made up of a plurality of semiconductor layers; and
a reflective film, which is formed on an end facet of the resonant cavity and includes a
first dielectric layer and a second dielectric layer having a refractive index greater than that of the
first dielectric layer,

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the device being characterized in that the second dielectric layer is made of niobium
oxide] The semiconductor laser device of Claim 1, wherein a refractive index of the second
dielectric layer is greater than a refractive index of the first dielectric layer.

5. (Currently amended) The semiconductor laser device of Claim [4] 1, [characterized in
that] wherein the first dielectric layer is made of silicon dioxide or aluminum oxide.

7. (Currently amended) The semiconductor laser device of Claim 4, [characterized in
that] wherein the [semiconductor layers] n-type compound semiconductor layer and the p-type
semiconductor layer are made of Group III - V nitride semiconductors.

8. (Currently amended) [A semiconductor laser device characterized by comprising:
a resonant cavity made up of a plurality of semiconductor layers; and
a reflective film, which is formed on an end facet of the resonant cavity by alternately
stacking first and second dielectric layers, each said second dielectric layer having a refractive
index greater than that of the first dielectric layers,

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the device being characterized in that at least one of the second dielectric layers, which is
closest to the end facet of the resonant cavity, is made of niobium oxide] The semiconductor

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laser device of claim 1, wherein the reflective film is formed by alternately laminating a plurality of first dielectric layers and a plurality of second dielectric layers containing niobium oxide.

12. (Currently amended) A method for fabricating a semiconductor laser device, [characterized by] said method comprising the steps of:

[forming a resonant cavity structure by] sequentially depositing [a plurality of semiconductor layers] a n-type compound semiconductor layer, a resonant cavity, and a p-type compound semiconductor layer on a substrate;

exposing an end facet of a resonant cavity [on the semiconductor layers] in an emitting direction by cleaving or etching the substrate [on which the semiconductor layers have been deposited]; and

forming a reflective film [containing niobium oxide] composed of a first dielectric layer and a second dielectric layer containing niobium oxide on the exposed end facet of the resonant cavity.

13. (Currently amended) The method of Claim 12, [characterized in that] wherein the step of forming the reflective film includes the step of [forming the reflective film as a multilayer structure including a first dielectric layer with a refractive index smaller than that of niobium oxide and a second dielectric layer of niobium oxide] alternately depositing a plurality of first dielectric layers and a plurality of second dielectric layers containing niobium oxide.